

L Number	Hits	Search Text	DB	Time stamp
1	2	5429708.pn.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/09 18:23
8	4758	porous near2 (si silicon)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/09 18:24
15	2059	(porous near2 (si silicon)) and device	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/09 18:30
22	15888	(pore or porosity) near3 (percent fraction "%" "5%" "10%" "15%" "20%" "25%" "30%")	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/09 18:30
29	335	(porous near2 (si silicon)) and ((pore or porosity) near3 (percent fraction "%" "5%" "10%" "15%" "20%" "25%" "30%"))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/09 18:30
36	139	((porous near2 (si silicon)) and ((pore or porosity) near3 (percent fraction "%" "5%" "10%" "15%" "20%" "25%" "30%"))) and device	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/09 18:43
43	81	((((porous near2 (si silicon)) and ((pore or porosity) near3 (percent fraction "%" "5%" "10%" "15%" "20%" "25%" "30%")))) and device) and (passivat\$3 protect\$3)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/09 18:43
50	142	(porous near2 (si silicon)) near16 (passivat\$3 protect\$3)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/09 18:44
57	4	((porous near2 (si silicon)) near16 (passivat\$3 protect\$3)) same organic	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/09 18:44

L Number	Hits	Search Text	DB	Time stamp
-	992	(polymer organic alkyl allyl hydrocarbon organo) near20 passivat\$3	EPO; JPO; DERWENT; IBM_TDB	2001/10/23 10:46
-	404	((polymer organic alkyl allyl hydrocarbon organo) near20 passivat\$3) and (semiconductor silicon si sige sic)	EPO; JPO; DERWENT; IBM_TDB	2001/10/23 10:49
-	73	((polymer organic alkyl allyl hydrocarbon organo) near20 passivat\$3) and (semiconductor silicon si sige sic)) and bond\$3	EPO; JPO; DERWENT; IBM_TDB	2001/10/22 18:11
-	5325	(semiconductor silicon si sige sic) near12 passivat\$3	EPO; JPO; DERWENT; IBM_TDB	2001/10/22 19:50
-	243	((polymer organic alkyl allyl hydrocarbon organo) near20 passivat\$3) and ((semiconductor silicon si sige sic) near12 passivat\$3)	EPO; JPO; DERWENT; IBM_TDB	2001/10/22 19:32
-	63438	(semiconductor silicon si sige sic) near12 (bond\$3 attach\$3)	EPO; JPO; DERWENT; IBM_TDB	2001/10/22 19:51
-	7506	((semiconductor silicon si sige sic) near12 (bond\$3 attach\$3)) near12 (polymer organic alkyl allyl hydrocarbon organo)	EPO; JPO; DERWENT; IBM_TDB	2001/10/22 19:54
-	37	((semiconductor silicon si sige sic) near12 (bond\$3 attach\$3)) near12 (polymer organic alkyl allyl hydrocarbon organo)) and passivat\$3	EPO; JPO; DERWENT; IBM_TDB	2001/10/22 19:54
-	118	(polymer organic alkyl allyl hydrocarbon organo) near15 (gate adj (dielectric insulator insulating insulation))	EPO; JPO; DERWENT; IBM_TDB	2001/10/22 20:18
-	1884	(polymer organic alkyl allyl hydrocarbon organo) near20 passivat\$3	USPAT; US-PGPUB	2001/10/23 10:47
-	375	((polymer organic alkyl allyl hydrocarbon organo) near20 passivat\$3) near20 (semiconductor silicon si sige sic)	USPAT; US-PGPUB	2001/10/23 10:52
-	227	((polymer organic alkyl allyl hydrocarbon organo) near20 passivat\$3) near20 (semiconductor silicon si sige sic)) and bond\$3	USPAT; US-PGPUB	2001/10/23 10:53
-	47	((polymer organic alkyl allyl hydrocarbon organo) near20 passivat\$3) near20 (semiconductor silicon si sige sic)) same bond\$3	USPAT; US-PGPUB	2001/10/23 10:53
-	139	((polymer organic alkyl allyl hydrocarbon organo) near20 passivat\$3) and ((chemical\$2 physical\$2 electrostatic electrostatically) near4 bond\$3)	USPAT; US-PGPUB	2001/10/23 10:56
-	36	((polymer organic alkyl allyl hydrocarbon organo) near20 passivat\$3) and ((chemical\$2 physical\$2 electrostatic electrostatically) near4 attach\$3)	USPAT; US-PGPUB	2001/10/23 10:56
-	152	((polymer organic alkyl allyl hydrocarbon organo) near20 passivat\$3) and ((chemical\$2 physical\$2 electrostatic electrostatically) near4 bond\$3)) ((polymer organic alkyl allyl hydrocarbon organo) near20 passivat\$3) and ((chemical\$2 physical\$2 electrostatic electrostatically) near4 attach\$3))	USPAT; US-PGPUB	2001/10/23 10:56
-	11	((polymer organic alkyl allyl hydrocarbon organo) near20 passivat\$3) and ((chemical\$2 physical\$2 electrostatic electrostatically) near4 (attach\$3 bond\$3) near12 (silicon semiconductor si sic sige))	USPAT; US-PGPUB	2001/10/23 11:16
-	400	(polymer organic organo alkyl allyl allylic hydrocarbon) same ((chemical\$2 physical\$2 electrostatic electrostatically) near4 (attach\$3 bond\$3) near12 (silicon semiconductor si sic sige))	USPAT; US-PGPUB	2001/10/23 11:19
-	313	(polymer organic organo alkyl allyl allylic hydrocarbon) near12 (chemical\$2 physical\$2 electrostatic electrostatically) near4 (attach\$3 bond\$3) near12 (silicon semiconductor si sic sige)	USPAT; US-PGPUB	2001/10/23 14:11
-	13	4476003.URPN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2001/10/23 13:21

-	198	(polymer organic organo alkyl allyl allylic hydrocarbon) near12 (covalent covalently) near4 (attach\$3 bond\$3) near12 (silicon semiconductor si sic sige)	USPAT; US-PGPUB	2001/10/23 14:23
-	92	((polymer organic organo alkyl allyl allylic hydrocarbon) near12 (covalent covalently) near4 (attach\$3 bond\$3) near12 (silicon semiconductor si sic sige)) and (protect\$3 passivat\$3)	USPAT; US-PGPUB	2001/10/23 14:31
-	34	((polymer organic organo alkyl allyl allylic hydrocarbon) near12 (covalent covalently) near4 (attach\$3 bond\$3) near12 (silicon semiconductor si sic sige)) and ((protect\$3 passivat\$3) near12 (substrate wafer silicon semiconductor si sige sic))	USPAT; US-PGPUB	2001/10/23 14:32
-	1	6132801.URPN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2001/10/23 14:44
-	0	6284317.URPN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2001/10/23 16:42
-	1	"5096733".PN.	USPAT	2001/10/23 15:09
-	1	"4902570".PN.	USPAT	2001/10/23 15:09
-	1	"4895889".PN.	USPAT	2001/10/23 15:09
-	1	"4781940".PN.	USPAT	2001/10/23 15:09
-	1	"4191587".PN.	USPAT	2001/10/23 15:09
-	1	"4093771".PN.	USPAT	2001/10/23 15:10
-	1	"3802909".PN.	USPAT	2001/10/23 15:10
-	0	5939150.URPN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2001/10/23 15:16
-	0	5429708.URPN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2001/10/23 17:17
-	1	"6132801".PN.	USPAT	2001/10/23 16:42
-	1	"5326738".PN.	USPAT	2001/10/23 16:43
-	1	"5017540".PN.	USPAT	2001/10/23 16:43
-	1	"2721812".PN.	USPAT	2001/10/23 16:44
-	1	5908692.URPN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2001/10/23 16:48
-	1	"5268621".PN.	USPAT	2001/10/23 16:49
-	1788	(contact via opening hole) near12 (protect\$3 passivat\$3) near12 (polymer organic alkyl allyl hydrocarbon organo)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2001/10/23 19:28
-	51	((contact via opening hole) near12 (protect\$3 passivat\$3) near12 (polymer organic alkyl allyl hydrocarbon organo)) near10 (silicon doped dopant)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2001/10/23 19:10
-	11	4608097.URPN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2001/10/23 18:05

-	143	((contact via opening hole) near12 (protect\$3 passivat\$3) near12 (polymer organic alkyl allyl hydrocarbon organo)) and (438/\$ 257/\$).ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2001/10/23 19:11
-	34	((contact via opening hole) near12 (protect\$3 passivat\$3) near12 (polymer organic alkyl allyl hydrocarbon organo)) near12 (oxidation oxidizing oxidising oxidized oxidised)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2001/10/23 19:29
-	0	438/309-378.ccls,icls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2001/10/24 11:22
-	5810	438/309-378.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2001/10/24 11:22
-	318	438/309-378.ccls. and ((dopant impurity) near3 source)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2001/10/24 11:23
-	212	438/309-378.ccls. and (((dopant impurity) near3 source) same diffus\$3)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2001/10/24 11:24
-	122	438/309-378.ccls. and (((dopant impurity) near3 source) same diffus\$3 same emitter)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2001/10/24 11:40
-	107	(dopant impurity) near3 source near20 (ti or titanium or zr or zirconium or hf or halfnium)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2001/10/24 12:46
-	18	((dopant impurity) near3 source near20 (ti or titanium or zr or zirconium or hf or halfnium)) near20 diffus\$3	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2001/10/24 11:46
-	117	(dopant impurity) near3 source near20 metal near20 diffus\$3	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2001/10/24 12:44
-	91	((dopant impurity) near3 source near10 metal) near20 diffus\$3	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2001/10/24 12:45
-	3	((dopant impurity) near3 source near10 metal) near20 diffus\$3 same (ti or titanium or zr or zirconium or hf or halfnium)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2001/10/24 12:46
-	20	((gate adj (dielectric insulator insulating insulation oxide)) near20 (high adj2 (k dielectric))) same (organic organo alkyl hydrocarbon allyl polymer)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2001/10/24 15:29

-	463	(gate adj (dielectric insulator insulating insulation oxide)) near20 (high adj2 (k dielectric))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2001/10/24 14:48
-	25	((gate adj (dielectric insulator insulating insulation oxide)) near20 (high adj2 (k dielectric))) same ferroelectric	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2001/10/24 15:19
-	41184	(photovoltaic or solar) near3 (cell device)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2001/10/24 15:20
-	337	((photovoltaic or solar) near3 (cell device)) and ("10.sup.19" or "10.sup.20")	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2001/10/24 15:26
-	178	((photovoltaic or solar) near3 (cell device)) and (("10.sup.19" or "10.sup.20") near12 (impurity impurities dopant As P B Sb arsenic phosphorous boron antimony))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2001/10/24 15:28
-	62	((((photovoltaic or solar) near3 (cell device)) and (("10.sup.19" or "10.sup.20") near12 (impurity impurities dopant As P B Sb arsenic phosphorous boron antimony))) and (organic organo alkyl hydrocarbon allyl polymer)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2001/10/24 15:29